

Title (en)

FIELD-EFFECT TRANSISTOR ON A SELF-ASSEMBLED SEMICONDUCTOR WELL

Title (de)

FELDEFFEKTTRANSISTOR AUF EINER SELBSTANGEORDNETEN HALBLEITERKAVITÄT

Title (fr)

TRANSISTOR A EFFET DE CHAMP SUR ILOT DE MATERIAU SEMICONDUCTEUR AUTO-ASSEMBLE

Publication

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Application

EP 11769841 A 20111006

Priority

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Abstract (en)

[origin: WO2012049071A1] The invention relates to a device comprising at least one transistor produced on a substrate (1) made of a first semiconductor, each transistor (20, 20) comprising: a gate electrode (5), called the gate; two conductive electrodes (3, 4); a well (2), made of a second semiconductor, embedded in the substrate (1) and defining a region able to form a channel, called the channel region; and an insulating region (6) separating the gate (5) from the two electrodes (3, 4) and from the channel region, characterized in that the channel region lies inside the well (2) and makes direct electrical contact with at least one of the two conductive electrodes (3, 4).

IPC 8 full level

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CPC (source: EP KR US)

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Citation (search report)

See references of WO 2012049071A1

Citation (examination)

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